Si2302DDS

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PRODUCT SUMMARY

 $R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V

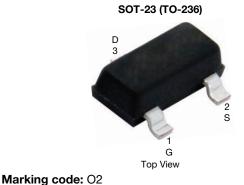
 $R_{DS(on)}$ max. (Ω) at V_{GS} = 2.5 V

V_{DS} (V)

I_D (A) Configuration

Q_g typ. (nC)

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20 0.057

0.075

3.5 2.9

Single

FEATURES

N-Channel 20 V (D-S) MOSFET

- TrenchFET[®] power MOSFET
- 100 % R_g tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Load switching for portable devices
- DC/DC converter



RoHS

N-Channel MOSFET

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	Si2302DDS-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \degree C$, unless otherwise noted)					
PARAMETER		SYMBOL	5 s	STEADY STATE	UNIT
Drain-source voltage		V _{DS}	20	20	V
Gate-source voltage		V _{GS}	± 8	± 8	
Continuous drain surrent (T 150 °C) a	T _A = 25 °C	- I _D	2.9	2.6	А
Continuous drain current (T _J = 150 °C) ^a	T _A = 70 °C		2.3	2.1	
Pulsed drain current (t = 300 µs) ^b		I _{DM}	10	10	A
Continuous source current (diode conduction) ^a		I _S	0.72	0.6	
Power dissipation ^a	T _A = 25 °C	P _D	0.86	0.71	W
	T _A = 70 °C		0.55	0.46	vv
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	-55 to +150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	t ≤ 5 s	R _{thJA}	120	145	
	Steady state		140	175	°C/W
Maximum junction-to-foot	Steady state	R _{thJF}	62	78	

Notes

a. Surface mounted on 1" x 1" FR4 board

b. Pulse width limited by maximum junction temperature

1

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•				
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	20	-	-	V	
Gate-threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.40	-	0.85	v	
Gate-body leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V	-	-	± 100	nA	
Zero gate voltage drain current		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA	
	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	-	-	75		
On-state drain current ^a	I _{D(on)}	$V_{DS}\!\geq$ 10 V, $V_{GS}\!=$ 4.5 V	6	-	-	А	
Drain-source on-resistance ^a		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 3.6 \text{ A}$	-	0.045	0.057	Ω	
	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 3.1 \text{ A}$	-	0.056	0.075		
Forward transconductance a	g _{fs}	$V_{DS} = 5 V, I_{D} = 3.6 A$	-	13	-	S	
Diode forward voltage	V _{SD}	$I_{S} = 0.95 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.7	1.2	V	
Dynamic ^b							
Total gate charge	Qg		-	3.5	5.5		
Gate-source charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 3.6 A	-	0.6	-	nC	
Gate-drain charge	Q _{gd}		-	0.45	-		
Gate resistance	Rg	f = 1 MHz	2	4	8	Ω	
Switching							
Turn-on delay time	t _{d(on)}		-	8	15		
Rise time	t _r	V_{DD} = 10 V, R_L = 2.78 Ω ,	-	7	15		
Turn-off delay time	t _{d(off)}	$I_D \cong 3.6$ A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	30	45	ns	
Fall time	t _f		-	7	15		
Source-drain reverse recovery time	t _{rr}	I _F = 3.6 A, di/dt = 100 A/μs	-	8.5	15		
Body diode reverse recovery charge	Q _{rr}	$r_{\rm F} = 3.0$ A, u/ul = 100 A/µS	-	2	4	nC	

Notes

a. Pulse test: Pulse width $\leq 300~\mu\text{s},\, \text{duty cycle} \leq 2~\%$

b. Guaranteed by design, not subject to production testing

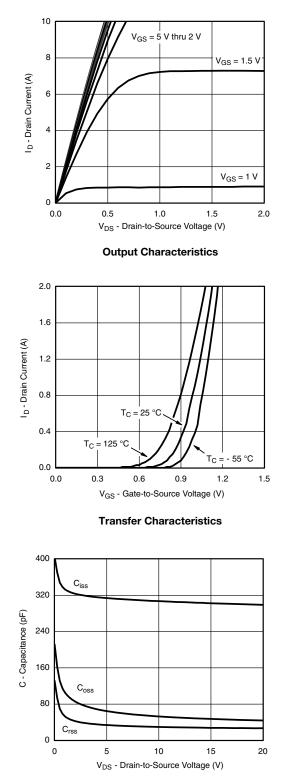
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

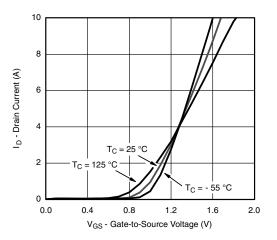


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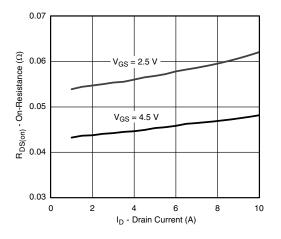
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

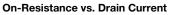


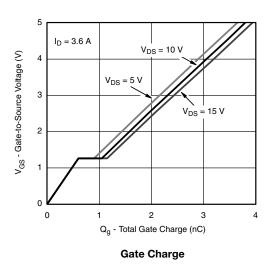
Capacitance



Transfer Characteristics







S11-2528-Rev. A, 26-Dec-11

3

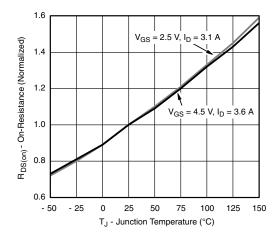
Document Number: 63653



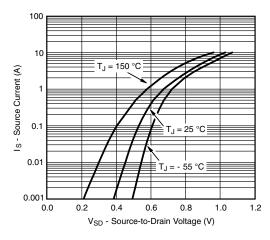
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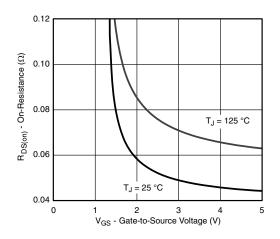
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



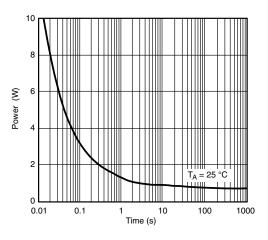
On-Resistance vs. Junction Temperature



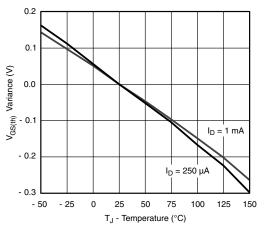
Source-Drain Diode Forward Voltage



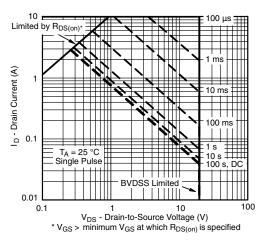
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power







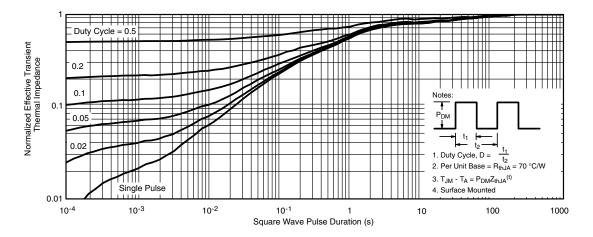
Safe Operating Area, Junction-to-Ambient



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63653.



Package Information

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SOT-23 (TO-236): 3-LEAD







Dim MilLI	MILLIN	METERS	INCHES		
	Max	Min	Мах		
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	



Application Note 826

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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